

Title (en)  
THIN-FILM SEMICONDUCTOR COMPONENT AND PRODUCTION METHOD FOR SAID COMPONENT

Title (de)  
DÜNNFILMHALBLEITERBAUELEMENT UND VERFAHREN ZU DESSEN HERSTELLUNG

Title (fr)  
COMPOSANT SEMI-CONDUCTEUR A COUCHE MINCE ET SON PROCEDE DE PRODUCTION

Publication  
**EP 1588409 A1 20051026 (DE)**

Application  
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Abstract (en)  
[origin: WO2004068567A1] The invention relates to a semiconductor component comprising a thin-film semiconductor body (2), which is located on a support (4) that contains germanium. The invention also relates to a method for producing a semiconductor component of this type.

IPC 1-7  
**H01L 21/20**; **H01L 21/762**; **H01L 33/00**

IPC 8 full level  
**H01L 21/18** (2006.01); **H01L 21/20** (2006.01); **H01L 21/683** (2006.01); **H01L 21/762** (2006.01); **H01L 23/00** (2006.01); **H01L 33/02** (2010.01); **H01L 33/00** (2010.01); **H01L 33/30** (2010.01)

CPC (source: EP KR US)  
**H01L 21/187** (2013.01 - EP US); **H01L 21/6835** (2013.01 - EP US); **H01L 24/29** (2013.01 - EP US); **H01L 24/83** (2013.01 - EP US); **H01L 33/00** (2013.01 - KR); **H01L 33/02** (2013.01 - EP US); **H01L 33/62** (2013.01 - KR); **H01L 33/0093** (2020.05 - EP US); **H01L 33/30** (2013.01 - EP US); **H01L 2221/68354** (2013.01 - EP US); **H01L 2224/29** (2013.01 - EP US); **H01L 2224/291** (2013.01 - EP US); **H01L 2224/29101** (2013.01 - EP US); **H01L 2224/29144** (2013.01 - EP US); **H01L 2224/29298** (2013.01 - EP US); **H01L 2224/83001** (2013.01 - EP US); **H01L 2224/8319** (2013.01 - EP US); **H01L 2224/83224** (2013.01 - EP US); **H01L 2224/83801** (2013.01 - EP US); **H01L 2224/83805** (2013.01 - EP US); **H01L 2924/00011** (2013.01 - EP US); **H01L 2924/00013** (2013.01 - EP US); **H01L 2924/01004** (2013.01 - EP US); **H01L 2924/01005** (2013.01 - EP US); **H01L 2924/01006** (2013.01 - EP US); **H01L 2924/0101** (2013.01 - EP US); **H01L 2924/01013** (2013.01 - EP US); **H01L 2924/01015** (2013.01 - EP US); **H01L 2924/01018** (2013.01 - EP US); **H01L 2924/01023** (2013.01 - EP US); **H01L 2924/01032** (2013.01 - EP US); **H01L 2924/01033** (2013.01 - EP US); **H01L 2924/01039** (2013.01 - EP US); **H01L 2924/01049** (2013.01 - EP US); **H01L 2924/0105** (2013.01 - EP US); **H01L 2924/01051** (2013.01 - EP US); **H01L 2924/0106** (2013.01 - EP US); **H01L 2924/01075** (2013.01 - EP US); **H01L 2924/01078** (2013.01 - EP US); **H01L 2924/01079** (2013.01 - EP US); **H01L 2924/0132** (2013.01 - EP US); **H01L 2924/01322** (2013.01 - EP US); **H01L 2924/014** (2013.01 - EP US); **H01L 2924/10329** (2013.01 - EP US); **H01L 2924/12036** (2013.01 - EP US); **H01L 2924/12041** (2013.01 - EP US); **H01L 2924/157** (2013.01 - EP US)

Citation (search report)  
See references of WO 2004068567A1

Citation (examination)  
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• WO 0233760 A1 20020425 - OSRAM OPTO SEMICONDUCTORS GMBH [DE], et al  
• JP 2001015798 A 20010119 - TOSHIBA CORP

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DE

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